

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

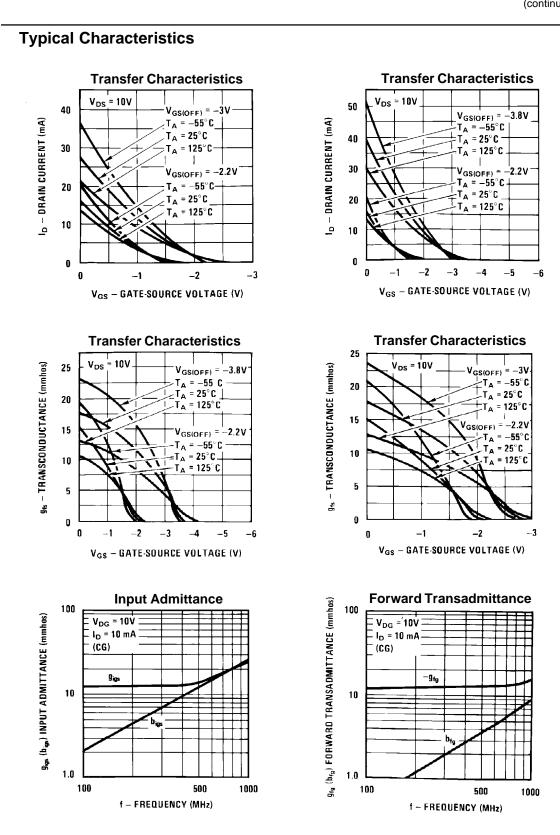
N-Channel RF Amplifie (continue							
Electr Symbol	ical Characteristics T	A = 25°C unless otherwise noted Test Conditions	Min	Тур	Max	Units	
Symbol	i diametei	Test conditions		тур	Wax	Onits	
OFF CHA	RACTERISTICS						
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$I_{G} = -1.0 \ \mu A, \ V_{DS} = 0$	- 25			V	
I _{GSS}	Gate Reverse Current	$V_{GS} = -15 V, V_{DS} = 0$ $V_{GS} = -15 V, V_{DS} = 0, T_A = 125^{\circ}C$			- 1.0 - 1.0	nA μA	
V _{GS(off)}	Gate-Source Cutoff Voltage	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1.0 \text{ nA}$ J309 J310	- 1.0 - 2.0		- 4.0 - 6.5	V V	
I _{DSS} V _{GS(f)}	Zero-Gate Voltage Drain Current* Gate-Source Forward Voltage	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \qquad \qquad \textbf{J309} \\ \textbf{J310} \\ V_{DS} = 0, \textbf{I}_{G} = 1.0 \text{ mA} \\ \end{cases}$	12 24		30 60 1.0	mA mA V	
SMALL S Re _(Yis)	IGNAL CHARACTERISTICS	V _{DS} = 10, I _D = 10 mA, f = 100 MHz	1				
	·			0.7		mmho	
		J309		0.7 0.5			
Re _(yos)	Common-Source Output Conductance			0.7 0.5 0.25		mmho	
(- <i>)</i>		J309 J310		0.5		mmho	
G _{pg}	Conductance	J309 J310 V _{DS} = 10, I _D = 10 mA, f = 100 MHz		0.5 0.25		mmho mmho dB	
Re _(Yos) 3 _{pg} Re _(Yfs) Re _(Yig)	Conductance Common-Gate Power Gain Common-Source Forward	$\label{eq:VDS} \begin{array}{c} J309\\ J310\\ \end{array}$ $V_{DS} = 10, I_{D} = 10 \text{mA}, f = 100 \text{MHz} \\ \end{array}$ $V_{DS} = 10, I_{D} = 10 \text{mA}, f = 100 \text{MHz} \\ \end{array}$		0.5 0.25 16		mmho mmho dB mmho	
G _{pg} Re ₍ y _{fs)} Re ₍ y _{ig)}	Conductance Common-Gate Power Gain Common-Source Forward Transconductance	$\label{eq:VDS} \begin{array}{c} J309\\ J310 \end{array}$ $V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz$ $V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz$ $V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz$ $V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz$ $V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ MHz$ $J309$	10,000	0.5 0.25 16 12	20,000	mmho mmho dB mmho mmho	
G _{pg} Re(Vfs) Re(Vig) Ifs	Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward	$\label{eq:VDS} \begin{array}{c} J309\\ J310 \end{array}$ $V_{DS} = 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz}$ $V_{DS} = 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz}$ $V_{DS} = 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz}$ $V_{DS} = 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz}$ $V_{DS} = 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz}$ $V_{DS} = 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz}$	10,000	0.5 0.25 16 12	20,000 18,000 150	mmho mmho dB mmho mmho µmho µmho	
G _{pg} Re ₍ y _{fs)}	Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output	$\label{eq:VDS} \begin{array}{c} J309\\ J310\\ \end{array}$ $V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ \text{kHz}\\ \hline J309\\ J310 \end{array}$,	0.5 0.25 16 12	18,000	mmho mmho dB mmho mmho µmho µmho	
Gpg Re(Vfs) Re(Vig) Ifs Idos	Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output Conductance	$\label{eq:J309} \begin{array}{c} J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ \hline J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ \hline J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ \hline J309\\ J310\\ \hline J309\\ \hline J309\\ J309\\ \hline J309\\ J309\\ \hline J309\\ J309\\ \hline J309\\$,	0.5 0.25 16 12 12 13,000	18,000	mmho mmho μmhos μmhos μmhos μmhos	
Spg Re(Vfs) Re(Vjg) Ifs Ios Ifg	Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output Conductance Common-Source Output Conductance Common-Gate Forward Conductance	$\label{eq:J309} \begin{array}{c} J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ \hline J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ \hline J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline J310\\ \hline$,	0.5 0.25 16 12 12 13,000 12,000 100	18,000	mmho mmho dB mmho μmho μmho μmho μmho μmho	
Bpg Re(Vfs) Re(Vfg) Ifs Ios Ifg Iog	Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Forward Transconductance Common-Source Output Conductance Common-Source Output Conductance Common-Gate Forward Conductance Common-Gate Output Conductance	$\label{eq:J309} \begin{array}{c} J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ MHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ \hline J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ kHz\\ J309\\ J310\\ \hline J31$,	0.5 0.25 16 12 12 13,000 12,000 100 150	18,000	mmho mmho dB mmho μmho μmho μmho μmho μmho μmho	
G _{pg} Re(Yfs) Re(Yig) Dfs Jos	Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output Conductance Common-Source Output Conductance Common-Gate Forward Conductance Common-Gate Forward Conductance Drain-Gate Capacitance	$\label{eq:spectral_states} \begin{array}{c} J309\\ J310\\ \hline \\ J310\\ \hline \\ V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline \\ V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline \\ V_{DS} = 10, \ I_D = 10 \ mA, \ f = 100 \ MHz\\ \hline \\ V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ MHz\\ \hline \\ V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ KHz\\ \hline \\ J309\\ J310\\ \hline \\ V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ KHz\\ \hline \\ J309\\ J310\\ \hline \\ V_{DS} = 10, \ I_D = 10 \ mA, \ f = 1.0 \ KHz\\ \hline \\ J309\\ J310\\ \hline \\ V_{DS} = 0, \ I_D = 10 \ mA, \ f = 1.0 \ KHz\\ \hline \\ J309\\ J310\\ \hline \\ \end{array}$,	0.5 0.25 16 12 12 13,000 12,000 100 150 2.0	18,000 150 2.5	mmho mmho dB mmho mmho µmho µmho µmho µmho pF	

*Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0%

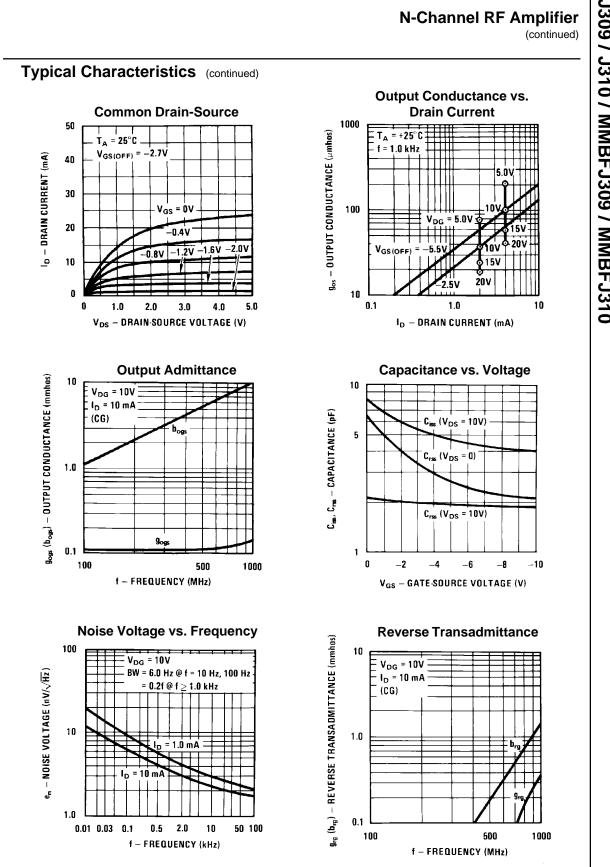
J309 / J310 / MMBFJ309 / MMBFJ310

N-Channel RF Amplifier

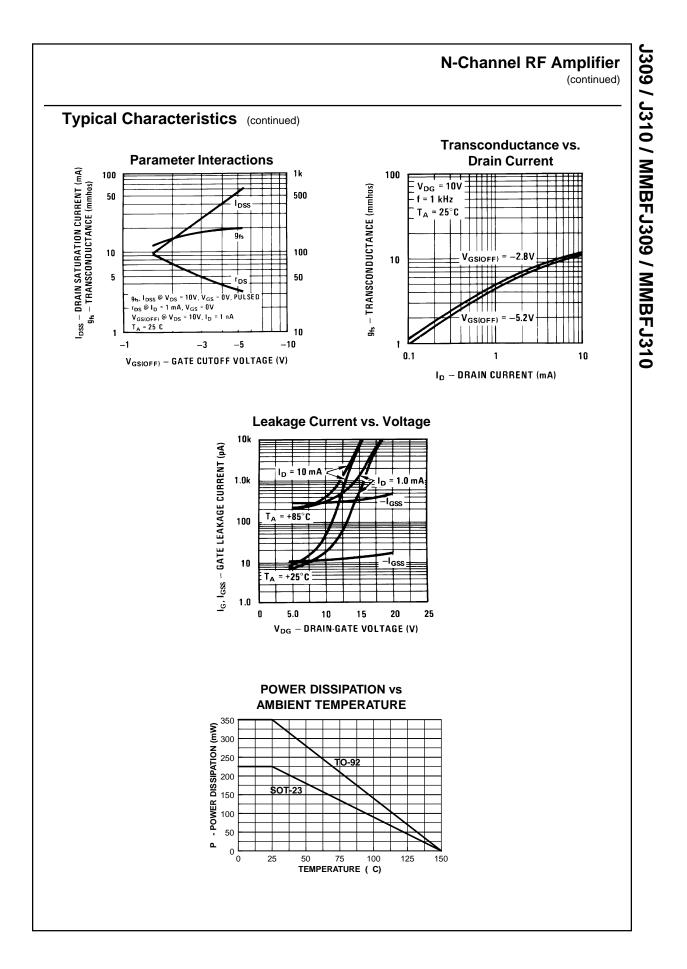
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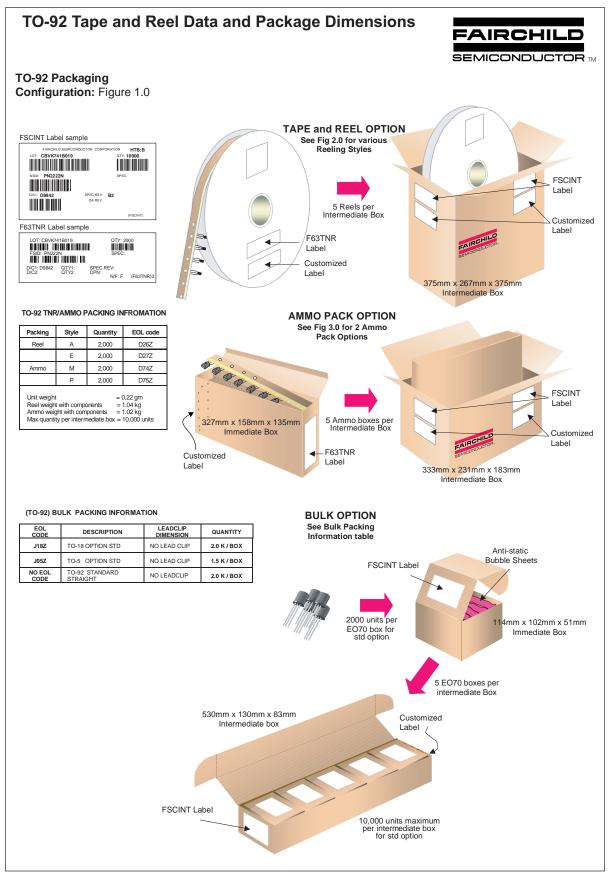


J309 / J310 / MMBFJ309 / MMBFJ310

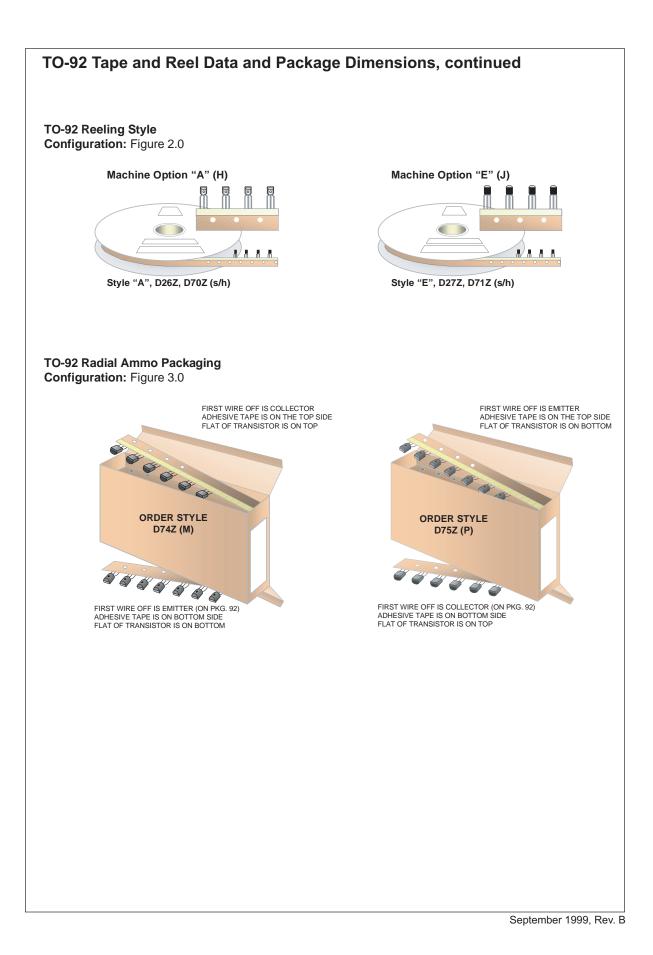


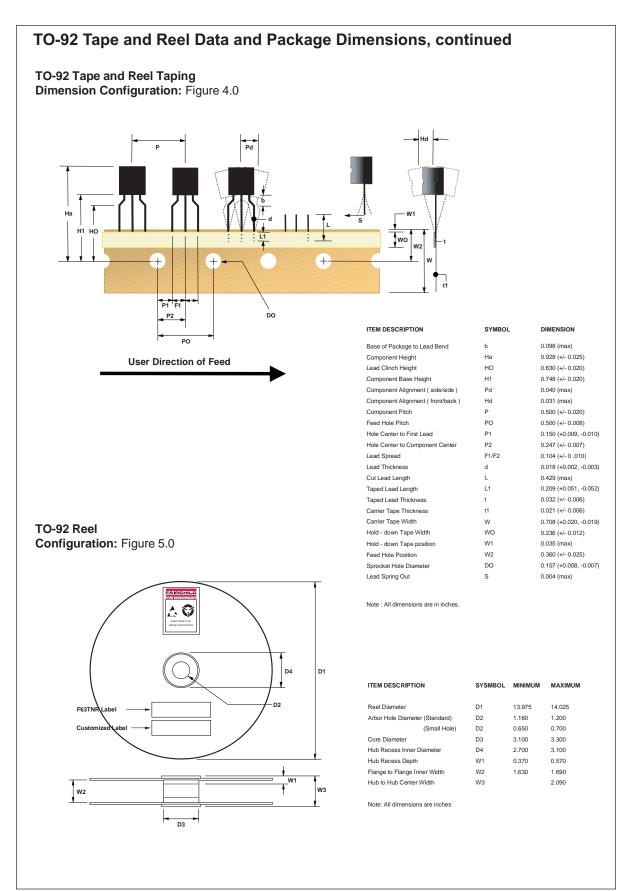
J309 / J310 / MMBFJ309 / MMBFJ310

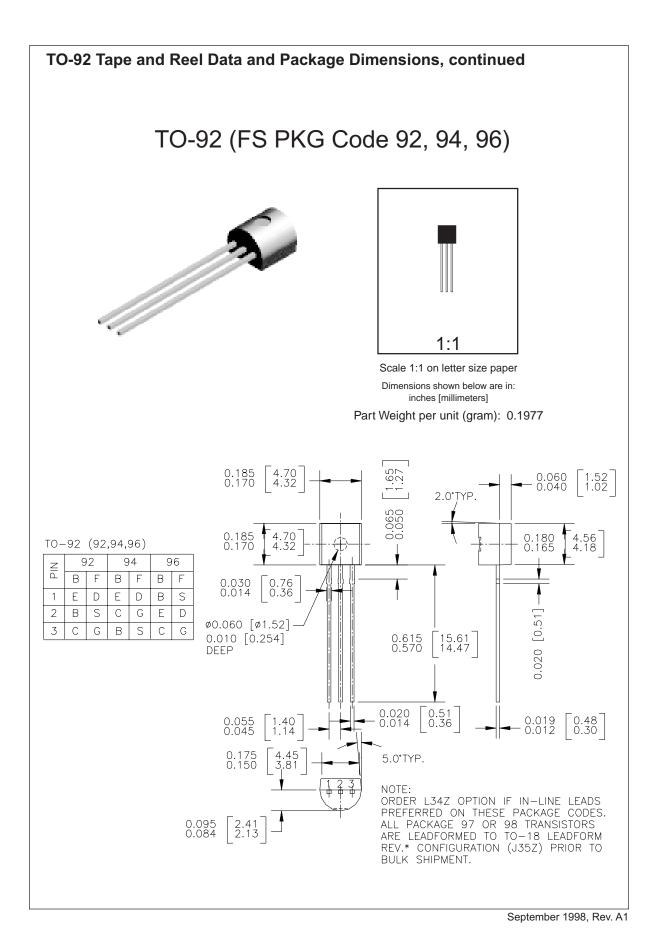


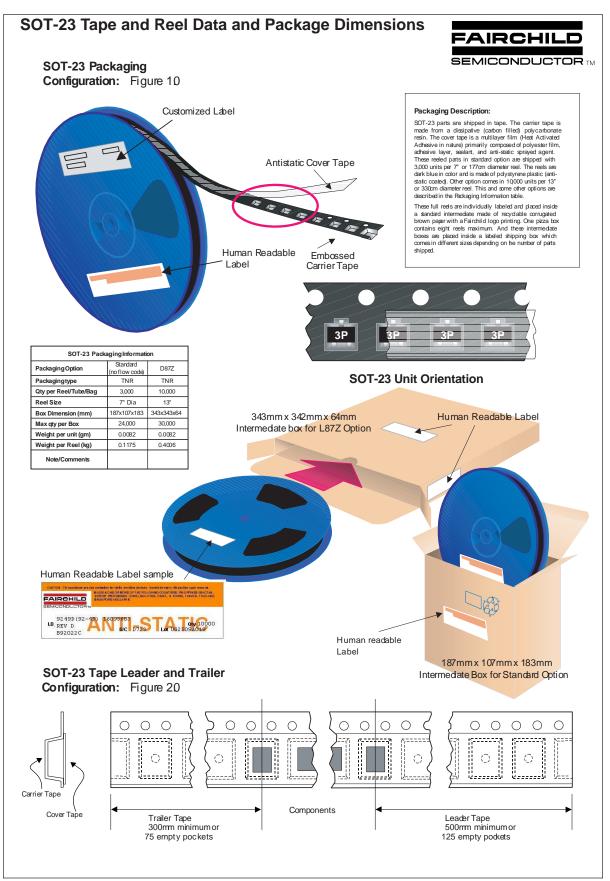


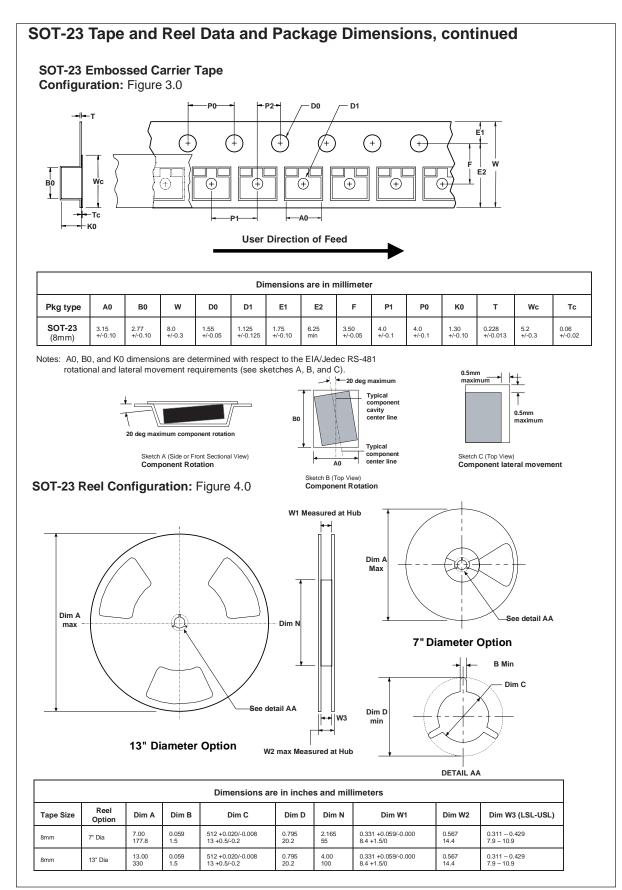
September 1999, Rev. B

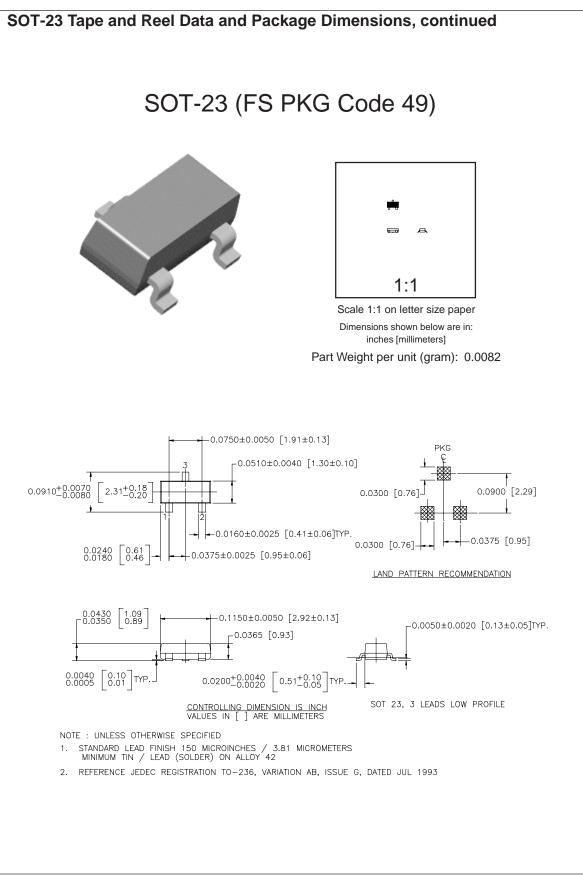












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